

*ABSTRACT AMENDMENT*

Replace the Abstract with:

The cleaning composition for removing resists includes a salt of hydrofluoric acid and a base not containing a metal (A component), a water-soluble organic solvent (B1 component), at least one ~~acid selected from a group consisting of~~ organic acid ~~and or~~ inorganic acid (C component), water (D component), and, optionally, an ammonium salt (E1 component), and ~~its hydrogen ion concentration (pH) is~~ having a pH 4-8. Thus, in ~~the manufacturing process of~~ a semiconductor device, such as a copper interconnecting process, ~~removing~~ efficiency of removing resist residue and other etching residue after etching or ashing ~~improves~~ is improved, and corrosion resistance of a copper and an insulating film ~~is~~ also ~~improves~~ improved.